PEOENED CENTRAL PAX CENTER MAY 0 4 2009

IN THE CLAIMS:

Claim 1 (canceled).

Claim 2 (currently amended): The surface-mount SAW device of claim [[1]] 5, characterized in that the electrical conductivity of said piezoelectric substrate is increased by heating an oxidizable element while holding it in contact with said piezoelectric substrate.

Claim 3 (currently amended): The surface-mount SAW device of claim [[1]] 5, characterized in that at least one of such motals as metal selected from the group consisting of Fe, Zr, Al Cr, Mn, Rh, Cu, V, W, U and Sn is contained as an impurity in said piezoelectric substrate to provide increased electrical conductivity of said piezoelectric substrate.

Claim 4 (original): The surface-mount SAW device of any one of claims [[1 to]] 2 or 3, characterized in that said piezoelectric substrate is made of LiTaO₃.

Claim 5 (currently amended): A surface-mount SAW device comprising:

a mounting substrate composed of an insulating substrate, external electrodes

mounted on the underside of said insulating substrate for surface mounting use, and conductor

traces arranged on the top of said insulating substrate and connected to said external

electrodes;

a SAW chip provided with a piezoelectric substrate, an IDT electrode formed on one surface of said piezoelectric substrate, and connection pads connected to said conductor traces via conductor bumps and flip chip mounted on said mounting substrate; and

sealing resin layer coated all over the outer surface of said flip-chip mounted SAW chip and down to the top surface of the mounting substrate to form an airtight space between said IDT electrode and said mounting substrate;

wherein the crystal structure of the piezoelectric substrate belongs to any one of point groups C₁, C₂, C₅, C_{2V}, C₄, C_{4V}, C₃, C_{3V}, C₆ and C_{6V} in terms of Schoenflies symbols; characterized in that:

said sealing resin layer has a relative dielectric constant of 3.2 or below and a volume resistivity of $1 \times 10^{16} \, \Omega$ cm or below;

the thickness H of the sealing resin layer on the top surface of said SAW chip is 0.02 mm or above; and

[[the]] <u>electrical</u> conductivity of said piezoelectric substrate is increased to suppress charging of the sealing resin layer.